



### **Product Summary**

BVDSS	Rds(ON) max	I <sub>D</sub> max T <sub>A</sub> = +25°C
	100mΩ @ V <sub>GS</sub> = -4.5V	-2.0A
-20V	120mΩ @ V <sub>GS</sub> = -2.5V	-1.9A
	160mΩ @ V <sub>GS</sub> = -1.8V	-1.6A

### Description

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

## **Applications**

- Motor Control
- Power Management Functions
- Backlighting

### P-CHANNEL ENHANCEMENT MODE MOSFET

### **Features and Benefits**

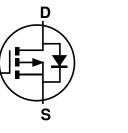
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/guality/product-definitions/</u>

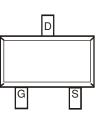
## **Mechanical Data**

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish—Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208<sup>(2)</sup>
- Weight: 0.006 grams (Approximate)



Top View





Top View

Internal Schematic

G

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2110UW-7	SOT323	3000/Tape & Reel
DMP2110UW-13	SOT323	10,000/Tape & Reel

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**

Notes:

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Cle	6	ΥM	
		П	

CI6 = Marking Code YM = Date Code Marking

 $\overline{Y}$  = Year (ex: H = 2020)

M = Month (ex: 9 = September)

Date Code Key												
Year	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	F	G	Н	I	J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage	VDSS	-20	V		
Gate-Source Voltage	V <sub>GSS</sub>	±12	V		
Continuous Drain Current (Note 6) V <sub>GS</sub> = -4.5V		TA = +25°C TA = +70°C	ID	-2.0 -1.6	A
Maximum Continuous Body Diode Forward Curre	nt (Note 6	ls	-0.9	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	l%) (Note	Ідм	-15	А	

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	0.49	W
Thermal Resistance, Junction to Ambient	Reja	253	°C/W
Total Power Dissipation (Note 6)	PD	0.65	W
Thermal Resistance, Junction to Ambient	Reja	192	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V, I_D = -250 \mu A$
Zero Gate Voltage Drain Current $T_J = +25^{\circ}C$	IDSS	_	_	-1.0	μΑ	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>			±100 ±800	nA	$\label{eq:VGS} \begin{split} V_{GS} &= \pm 8 V, \ V_{DS} = 0 V \\ V_{GS} &= \pm 12 V, \ V_{DS} = 0 V \end{split}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.4		-0.9	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
			63	100		$V_{GS} = -4.5V, I_D = -1.5A$
Static Drain-Source On-Resistance	RDS(ON)	—	75	120 160	mΩ	$V_{GS} = -2.5V, I_D = -1.2A$
			89			$V_{GS} = -1.8V, I_{D} = -1A$
Diode Forward Voltage	V <sub>SD</sub>	-	-0.7	-1.0	V	$V_{GS} = 0V, I_{S} = -1.0A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	-	443	_	pF	
Output Capacitance	Coss	-	59	_	pF	Vps = -6V, Vgs = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss		47		pF	
Gate Resistance	RG		8.5		Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1.0MHz$
Total Gate Charge	Qg	_	6.0	_	nC	
Gate-Source Charge	Qgs	_	0.6	_	nC	VGS = -4.5V, VDS = -10V, ID = - 3A
Gate-Drain Charge	Qgd	_	1.8	_	nC	
Turn-On Delay Time	tD(ON)	_	4.0	_	ns	
Turn-On Rise Time	tR	_	3.7	_	ns	V <sub>DS</sub> = -10V, V <sub>GS</sub> = -4.5V,
Turn-Off Delay Time	tD(OFF)	_	24.5	_	ns	$R_L = 10\Omega, R_G = 1.0\Omega, I_D = -1A$
Turn-Off Fall Time	tF	_	9.5	_	ns	7
Reverse Recovery Time	trr		8.3		ns	IF = -1.0A, di/dt = 100A/µs
Reverse Recovery Charge	QRR		2.0		nC	IF = -1.0A, di/dt = 100A/µs

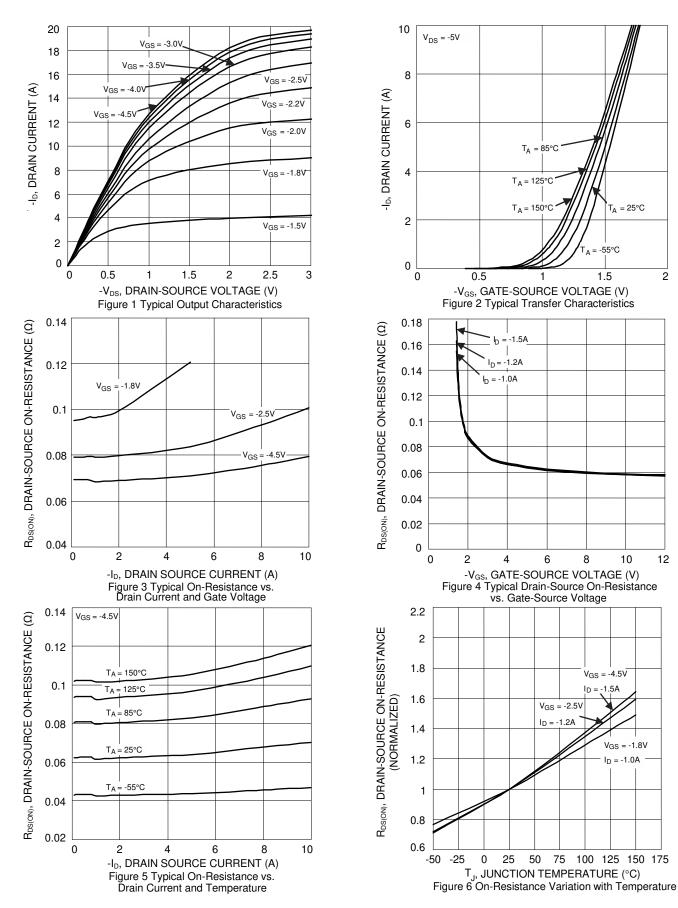
 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing. Notes:



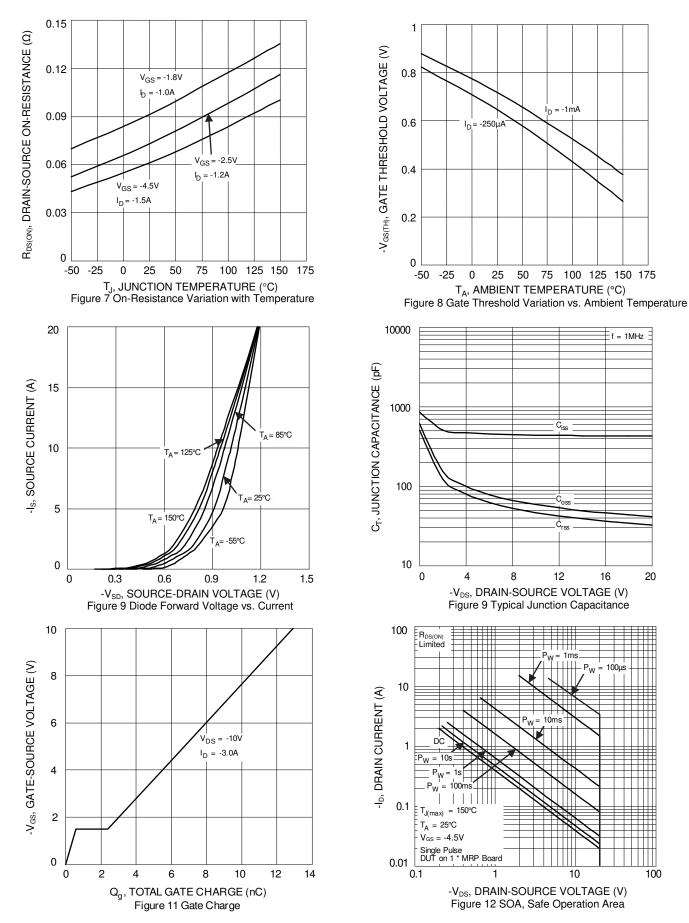
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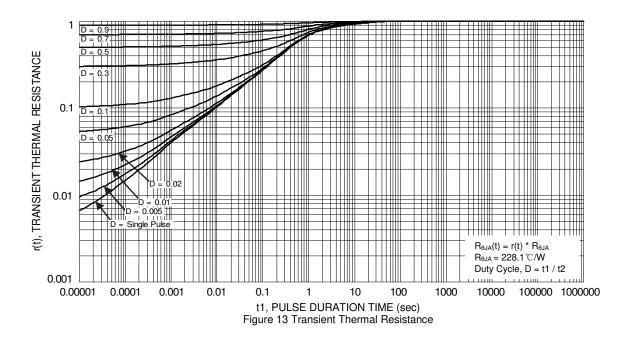






DMP2110UW Document number: DS41139 Rev. 4 - 2



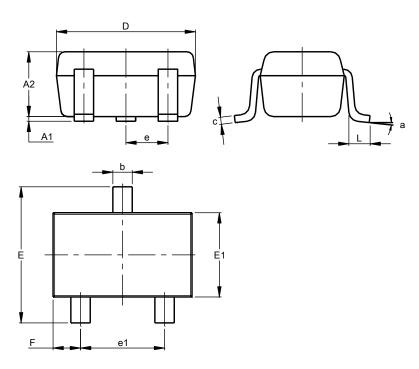




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

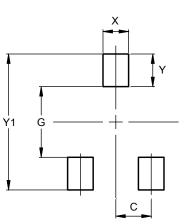
### SOT323



SOT323								
Dim	Min	Max	Тур					
A1	0.00	0.10	0.05					
A2	0.90	1.00	0.95					
b	0.25	0.40	0.30					
С	0.10	0.18	0.11					
D	1.80	2.20	2.15					
Е	2.00	2.20	2.10					
E1	1.15	1.35	1.30					
е	C	).650 B	SC					
e1	1.20	1.40	1.30					
F	0.375	0.475	0.425					
L	0.25	0.40	0.30					
а	0°	8°						
All	Dimen	sions i	in mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.470
Y	0.600
Y1	2.500

SOT323



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